

BUK7Y65-100E

N-channel 100 V, 65 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|---|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 19 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 64 | W |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$ | | - | 44 | 65 | mΩ |
| Dynamic characteristics | | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13; Fig. 14$ | | - | 7 | - | nC |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|----------------|
| 1 | S | source | mb | D I |
| 2 | S | source | | |
| 3 | S | source | [qj | G T T T |
| 4 | G | gate | <u>o o o o</u> | mbb076 S |
| mb | D | mounting base; connected to drain | 1 2 3 4 LFPAK56; Power- SO8 (SOT669) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|-----------------------|--|---------|--|--|
| | Name | Description | Version | | |
| BUK7Y65-100E | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| BUK7Y65-100E | 76510E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|-----|------|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 100 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | - | 100 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | -20 | 20 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | - | 19 | Α |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u> | - | 13.4 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4 | - | 76 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | - | 64 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------------------|--|---|--------|-----|------|------|
| T _j | junction temperature | | | -55 | 175 | °C |
| Source-drain diode | | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 19 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 76 | Α |
| Avalanche ru | ggedness | | | | | |
| E _{DS(AL)} S | non-repetitive drain-source avalanche energy | I_D = 19 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3 | [1][2] | - | 25.3 | mJ |

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

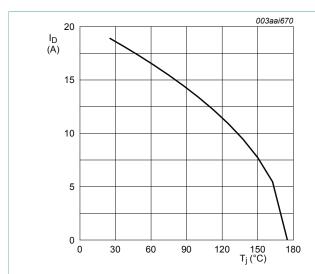


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

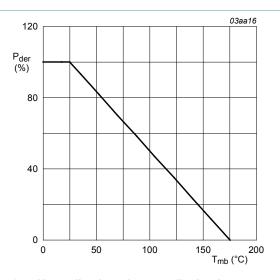


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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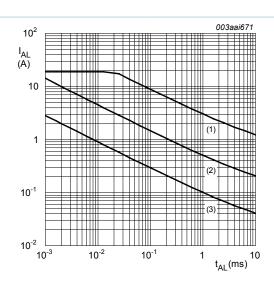


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j \ (init)} = 25 \,^{\circ}C$; (2) $T_{j \ (init)} = 150 \,^{\circ}C$; (3) Repetitive Avalanche

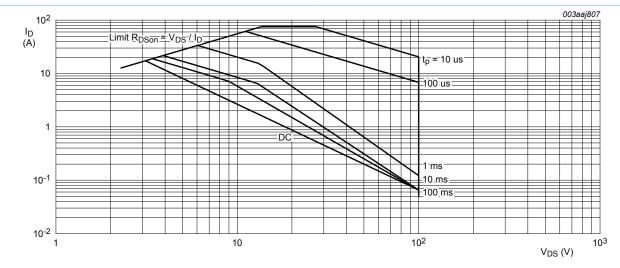


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

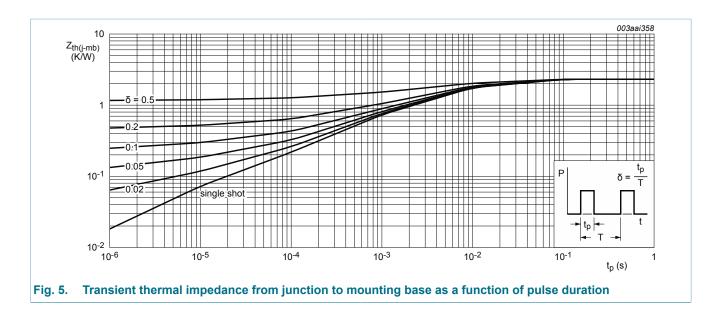
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|------------|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | _ | - | 2.31 | K/W |

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-------------------------------|--|-----|------|-----|------|
| Static chara | acteristics | | ' | | | _ |
| $V_{(BR)DSS}$ | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ | 100 | - | - | V |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$ | 90 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9 | 1 | - | - | V |
| I _{DSS} | drain leakage current | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.03 | 1 | μΑ |
| | | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u> | - | 44 | 65 | mΩ |
| resistance | | V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | - | 180 | mΩ |
| Dynamic ch | naracteristics | | ' | | | |
| Q _{G(tot)} | total gate charge | I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; | - | 17.8 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13; Fig. 14</u> | - | 3.4 | - | nC |
| Q_{GD} | gate-drain charge | | - | 7 | - | nC |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|------------------------------|---|--|-----|------|-------|------|
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u> | | - | 768 | 1023 | pF |
| C _{oss} | output capacitance | | | - | 99.5 | 119.4 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 74.2 | 101.7 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R_{L} = 10 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C | | - | 5.3 | - | ns |
| t _r | rise time | | | - | 7.5 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | | - | 12.4 | - | ns |
| t _f | fall time | | | - | 8 | - | ns |
| Source-dra | nin diode | | | | | | J |
| V _{SD} | source-drain voltage | $I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$ | | - | 0.82 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; \text{ T}_j = 25 \text{ °C}$ | | - | 31.5 | - | ns |
| Q _r | recovered charge | | | - | 40.6 | _ | nC |

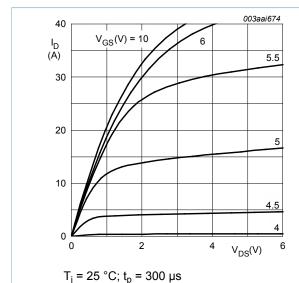


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

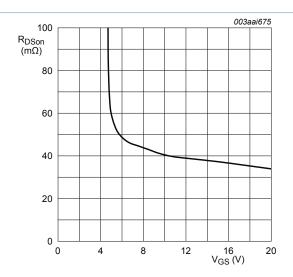


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

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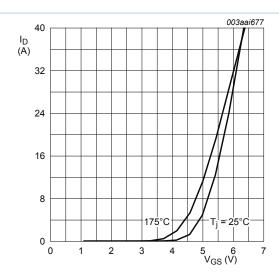


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

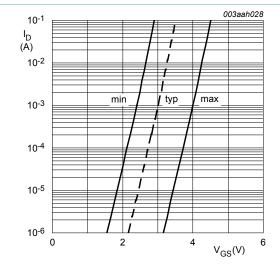


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

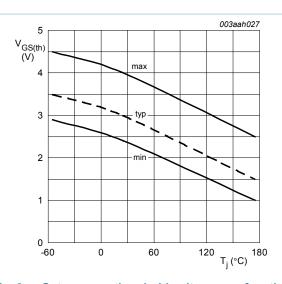
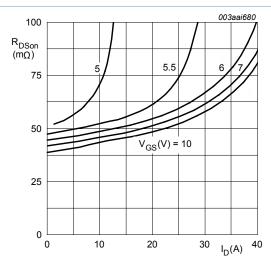


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$



 T_i = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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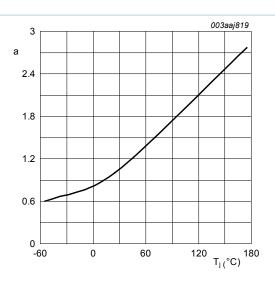


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

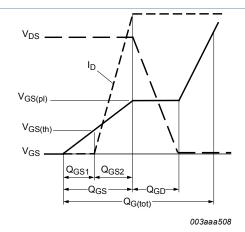


Fig. 14. Gate charge waveform definitions

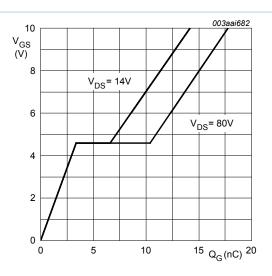


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; \ I_D = 5A$$

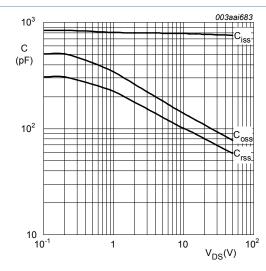


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

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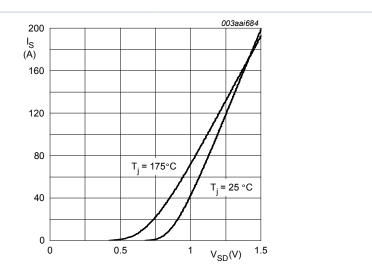


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

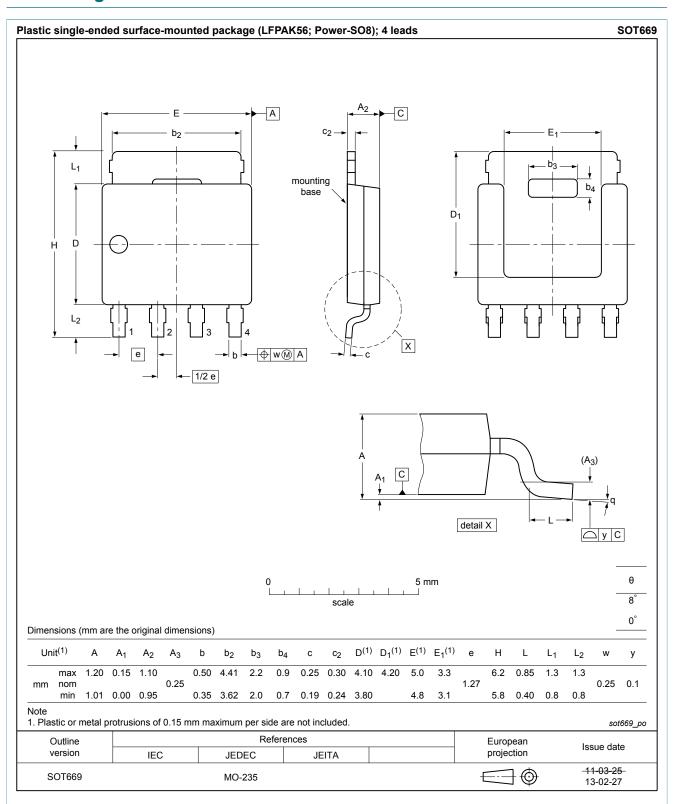


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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|--------------------------------------|--------------------|---|
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